



JMSH1504ASQ

## 150V 4.0mΩ N-Ch Power MOSFET

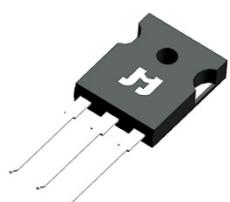
## Features

- Low ON-resistance,  $R_{DS(ON)}$
- Low Gate Charge,  $Q_g$
- 100% UIS and  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

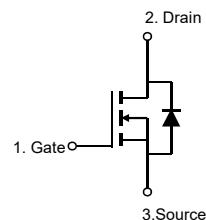
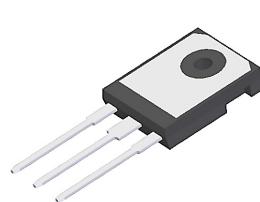
## Product Summary

Parameter	Value	Unit
$V_{DS}$	150	V
$V_{GS(th)}_{Typ}$	3.2	V
$I_D (@ V_{GS} = 10V)^{(1)}$	230	A
$R_{DS(ON)}_{Typ} (@ V_{GS} = 10V)$	4.0	mΩ

TO-247-3L Top View



TO-247-3L Bottom View

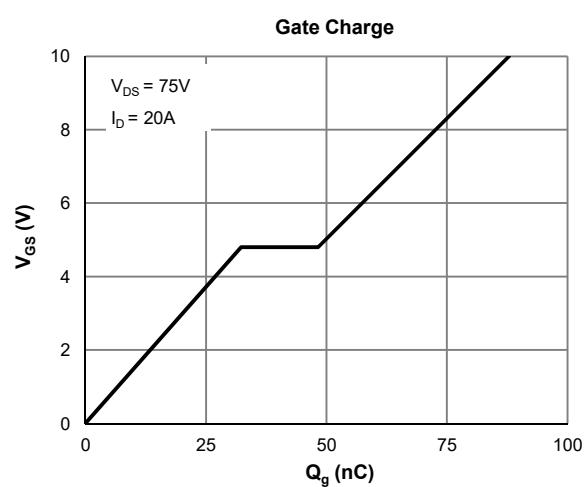
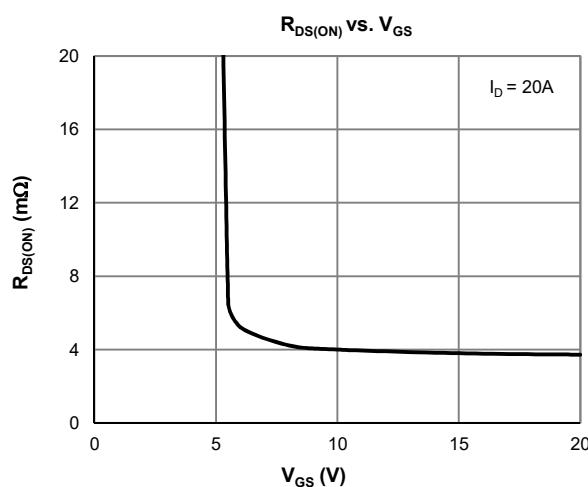


## Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH1504ASQ-U	TO-247-3L	3	SH1504A	NA	-55 to 175	Tube	30

Absolute Maximum Ratings (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	150	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current (1)	$I_D$	230	A
		163	
Pulsed Drain Current (2)	$I_{DM}$	920	A
Avalanche Current (3)	$I_{AS}$	77	A
Avalanche Energy (3)	$E_{AS}$	889	mJ
Power Dissipation (4)	$P_D$	600	W
		300	
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C



**Electrical Characteristics (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{DS} = 120\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.2	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(\text{ON})}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		4.0	4.9	$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		64		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.68	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			600	A
<b>DYNAMIC PARAMETERS<sup>(5)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 75\text{V}, f = 1\text{MHz}$		6540		pF
Output Capacitance	$C_{oss}$			772		pF
Reverse Transfer Capacitance	$C_{rss}$			6.7		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.4		$\Omega$
<b>SWITCHING PARAMETERS<sup>(5)</sup></b>						
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0$ to $10\text{V}$ $V_{DS} = 75\text{V}, I_D = 20\text{A}$		88		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$ )	$Q_g$			57		nC
Gate Source Charge	$Q_{gs}$			32		nC
Gate Drain Charge	$Q_{gd}$			16.0		nC
Turn-On DelayTime	$t_{D(\text{on})}$	$V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$ $R_L = 3.8\Omega, R_{\text{GEN}} = 6\Omega$		48		ns
Turn-On Rise Time	$t_r$			90		ns
Turn-Off DelayTime	$t_{D(\text{off})}$			94		ns
Turn-Off Fall Time	$t_f$			60		ns
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		122		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		279		nC

**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	48	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.25	0.30	$^\circ\text{C}/\text{W}$

**Notes:**

1. Computed continuous current assumes the condition of  $T_{J_{\text{Max}}}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J_{\text{Max}}} = 175^\circ\text{C}$ .
3. This single-pulse measurement was taken under the following condition [ $L = 300\mu\text{H}, V_{GS} = 10\text{V}, V_{DD} = 75\text{V}$ ] while its value is limited by  $T_{J_{\text{Max}}} = 175^\circ\text{C}$ .
4. The power dissipation  $P_D$  is based on  $T_{J_{\text{Max}}} = 175^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

### Typical Electrical & Thermal Characteristics

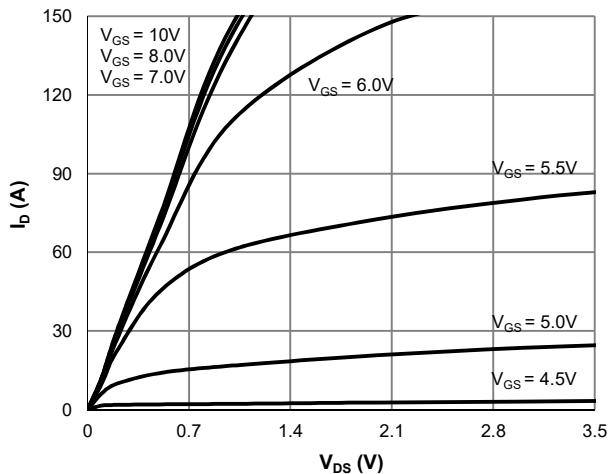


Figure 1: Saturation Characteristics

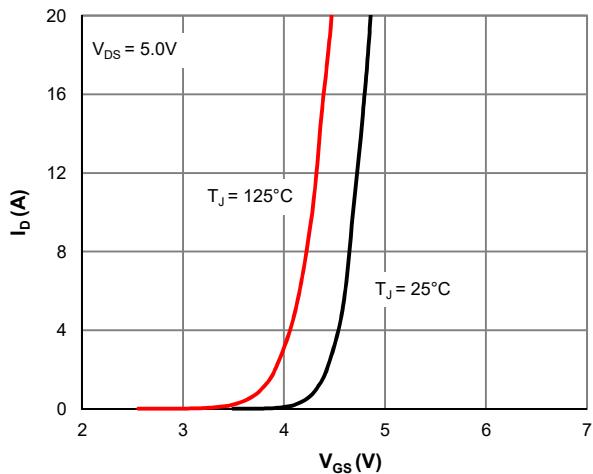


Figure 2: Transfer Characteristics

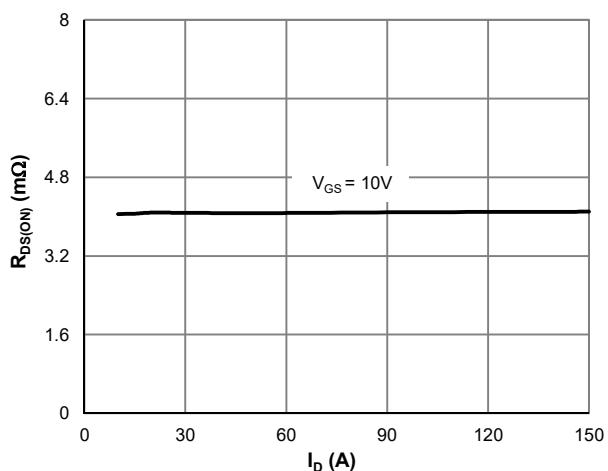


Figure 3:  $R_{DS(\text{ON})}$  vs. Drain Current

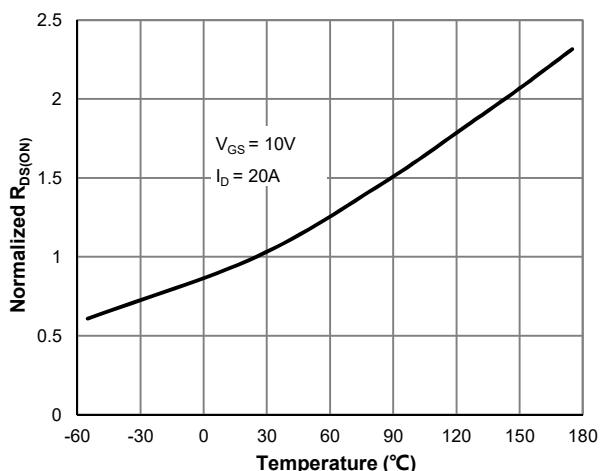


Figure 4:  $R_{DS(\text{ON})}$  vs. Junction Temperature

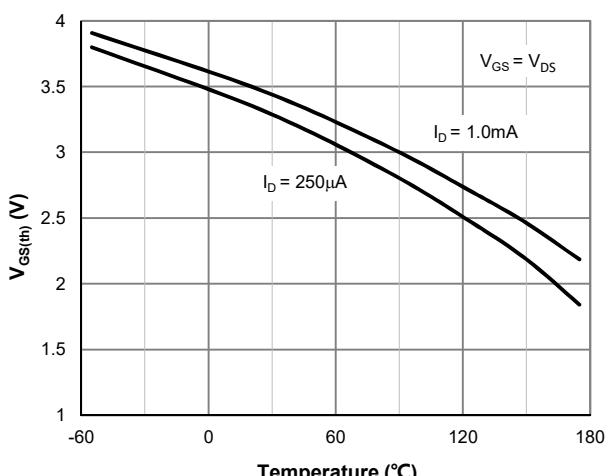


Figure 5:  $V_{GS(\text{th})}$  vs. Junction Temperature

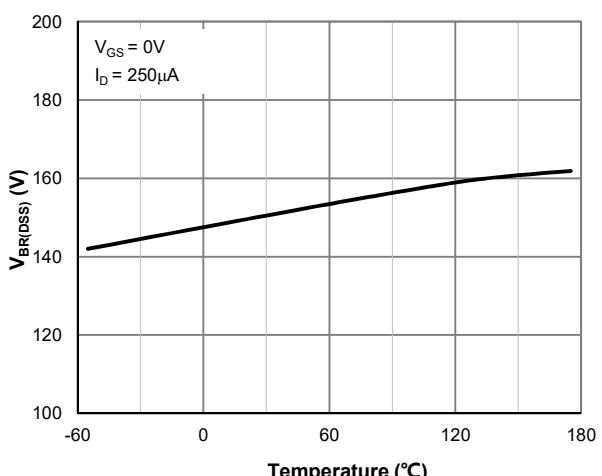
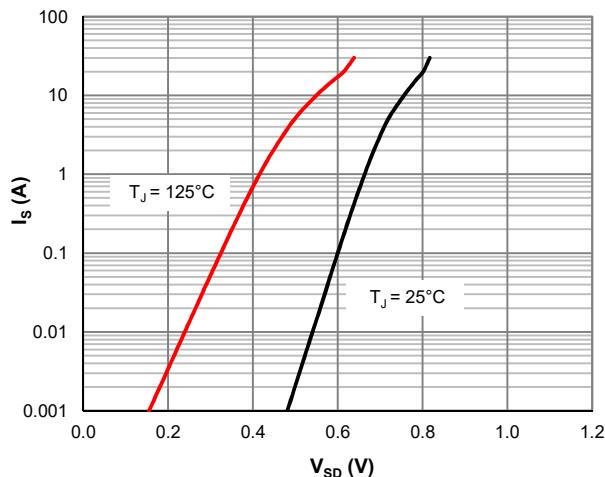
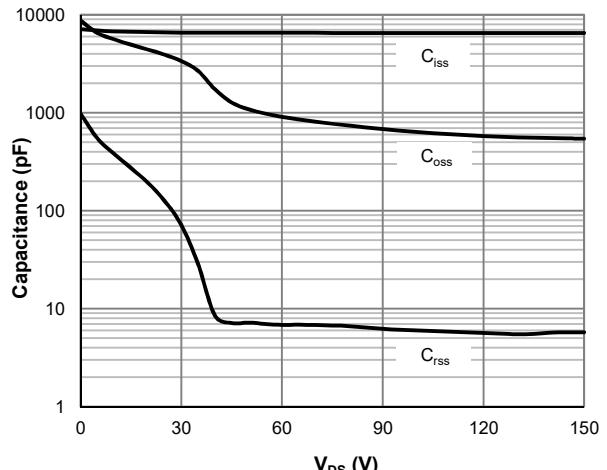


Figure 6:  $V_{BR(\text{DSS})}$  vs. Junction Temperature

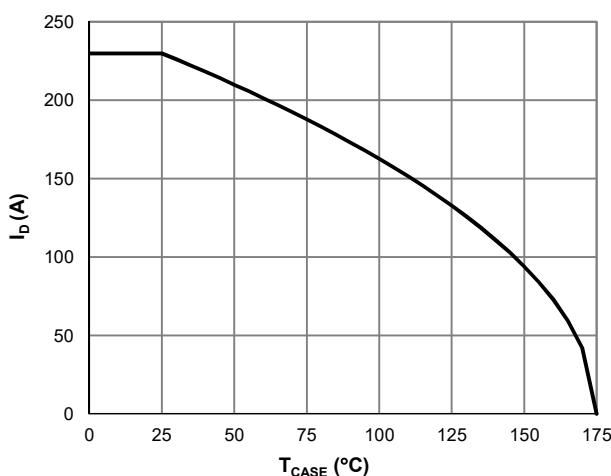
### Typical Electrical & Thermal Characteristics



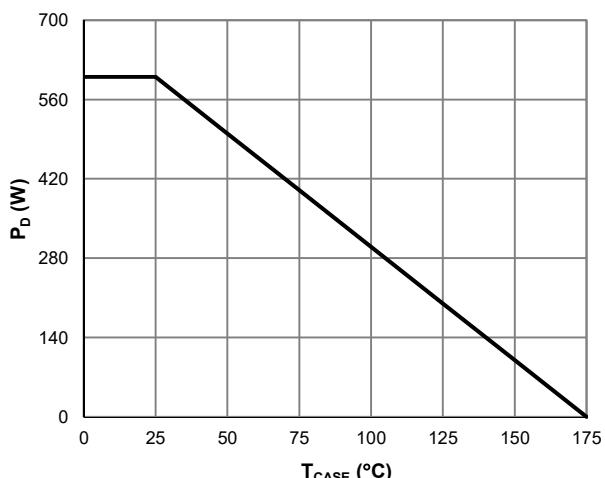
**Figure 7: Body-Diode Characteristics**



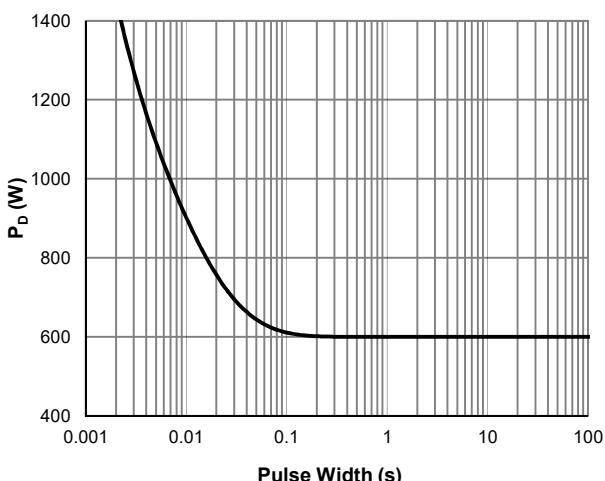
**Figure 8: Capacitance Characteristics**



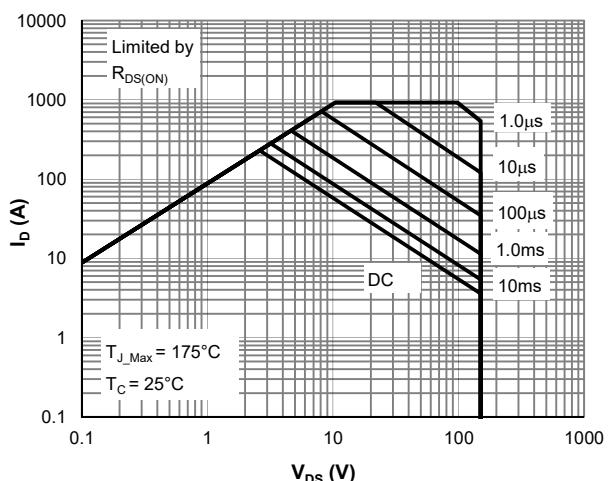
**Figure 9: Current De-rating**



**Figure 10: Power De-rating**



**Figure 11: Single Pulse Power Rating, Junction-to-Case**



**Figure 12: Maximum Safe Operating Area**

### Typical Electrical & Thermal Characteristics

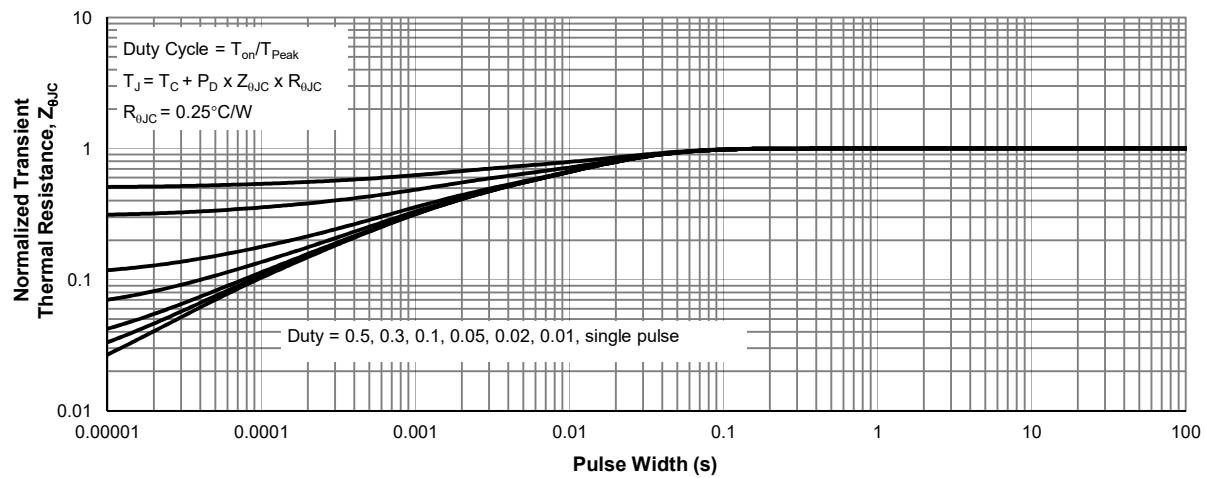
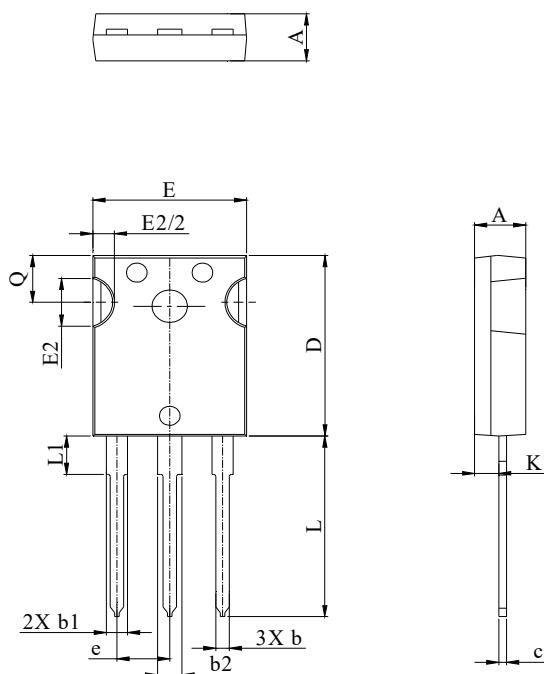


Figure 13: Normalized Maximum Transient Thermal Impedance

## TO-247-3L Package Information

## Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.80	5.02	5.21
b	1.00	1.20	1.40
b1	1.90	2.00	2.39
b2	2.87	3.00	3.22
c	0.41	0.60	0.79
D	20.80	21.00	21.20
E	15.50	15.94	16.13
E2	4.32		5.49
L	19.70	20.07	20.32
L1	4.00		4.40
K	2.20		2.50
e	5.44 BSC		